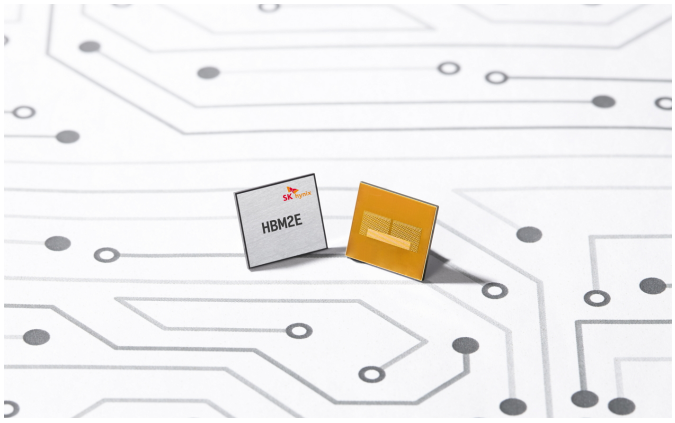
SK Hynix announces a High Bandwidth Memory (HBM) update-- HBM2E DRAM promising "the industry's highest bandwidth" in the shape of a 50% bandwidth increase and 100% additional capacity over the previous HBM2.



According to the company, HBM2E supports bandwidth reaching over 460GB per second, based on 3.6Gbps performance per pin with 1024 data I/Os. TSV (Through Silicon Via) technology allows the vertical stacking of a maximum of eight 16Gb chips, creating a single, dense package with 16GB data capacity.

The announcement press release points out HBM2E memory will find use in applications such as high-end GPUs, supercomputers, machine learning and artificial intelligence systems demanding maximum memory performance, Unlike commodity DRAM products, HBM chips are interconnected closely to the processor, allowing for even faster data transfer.

SK Hynix says HBM2E mass production starts on 2020.

Go SK Hynix Develops World's Fastest High Bandwidth Memory, HBM2E